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**12 V, single P-channel Trench MOSFET** 22 November 2012

Product data sheet

## 1. Product profile

### 1.1 General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### **1.2 Features and benefits**

- 1.5 kV ESD protection (human body model)
- Trench MOSFET technology
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- Exposed drain pad for excellent thermal conduction
- Tin-plated 100 % solderable side pads for optical solder inspection

### **1.3 Applications**

- Charging switch for portable devices
- DC-to-DC converters
- Power management in battery-driven portable devices
- Hard disk and computing power management

### 1.4 Quick reference data

Table 1. Qui	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	-12	V
V <sub>GS</sub>	gate-source voltage	-		-12	-	12	V
I <sub>D</sub>	drain current	$V_{GS}$ = -4.5 V; $T_{amb}$ = 25 °C; t ≤ 5 s	[1]	-	-	-11.8	А
Static characteristics							
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = -4.5 V; I <sub>D</sub> = -8.2 A; T <sub>j</sub> = 25 °C		-	15	19	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.





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12 V, single P-channel Trench MOSFET

# 2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain		D L
2	D	drain		
3	G	gate		G
4	S	source		\$ 017aaa257
5	D	drain	Transparent top view	
6	D	drain	DFN2020MD-6 (SOT1220)	
7	D	drain		
8	S	source		

# 3. Ordering information

Table 3. Ordering inf	formation					
Type number	Package					
	Name	Description	Version			
PMPB15XP	DFN2020MD-6	plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1220			

# 4. Marking

Table 4. Marking codes	
Type number	Marking code
PMPB15XP	1A

# 5. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-12	V
V <sub>GS</sub>	gate-source voltage			-12	12	V
I <sub>D</sub>	drain current	$V_{GS}$ = -4.5 V; $T_{amb}$ = 25 °C; t ≤ 5 s	[1]	-	-11.8	А
		V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-8.2	А
		V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	-5.2	А
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	-33	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[1]	-	1.7	W
Ptot PMPB15XP	· ·	I amb = 25 °C	[1]		1.7 XP B.V. 2012.	A

# PMPB15XP

#### 12 V, single P-channel Trench MOSFET

Symbol	Parameter	Conditions		Min	Max	Unit
		T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	3.5	W
		T <sub>sp</sub> = 25 °C		-	12.5	W
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drain diode						
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	-1.9	А

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

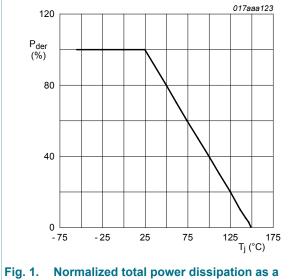


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

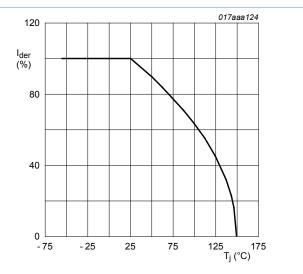


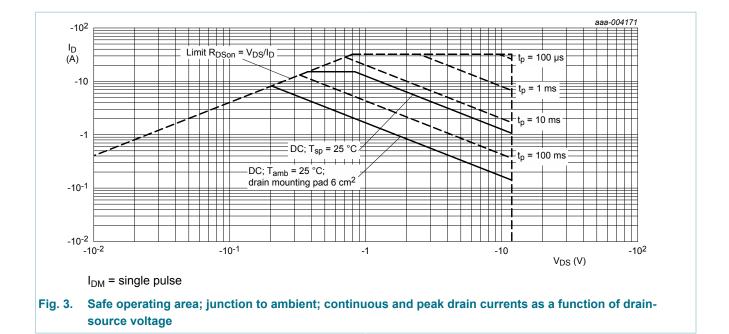
Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^\circ C)}} \times 100 \%$$

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#### 12 V, single P-channel Trench MOSFET



# 6. Thermal characteristics

Table 6. T	Thermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
ung-a)	thermal resistance	in free air	[1]	-	235	270	K/W
	from junction to ambient		[2]	-	67	74	K/W
	ambient	in free air; t ≤ 5 s	[2]	-	33	36	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	5	10	K/W

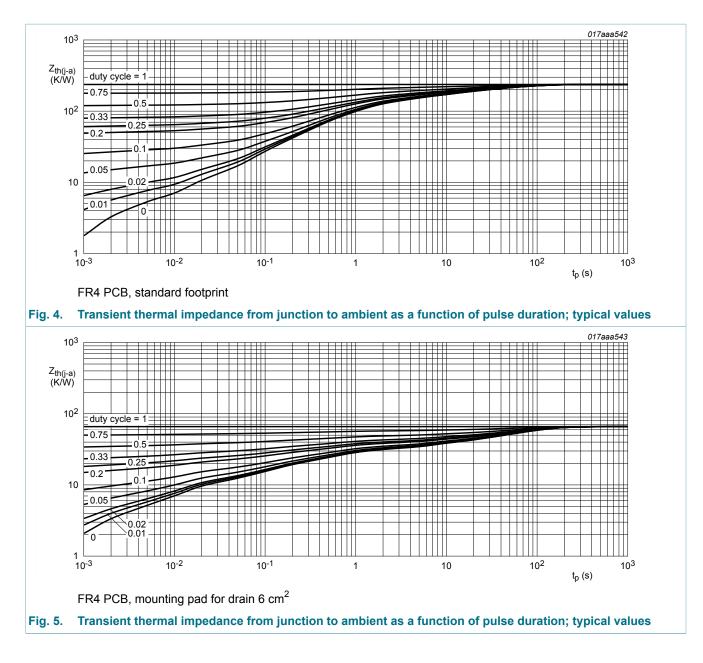
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

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## 7. Characteristics

Table 7. Cha	aracteristics						
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
Static charact	teristics	·					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D$ = -250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C		-12	-	-	V
V <sub>GSth</sub>	gate-source threshold voltage	I <sub>D</sub> = -250 μA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 25 °C		-0.47	-0.68	-0.9	V
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = -12 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C		-	-	-1	μA
		V <sub>DS</sub> = -12 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 150 °C		-	-	-100	μA
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = -12 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	-100	nA
		$V_{GS}$ = 12 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	-100	nA
R <sub>DSon</sub>	drain-source on-state	$V_{GS}$ = -4.5 V; I <sub>D</sub> = -8.2 A; T <sub>j</sub> = 25 °C	-	15	19	mΩ
	resistance	$V_{GS}$ = -4.5 V; I <sub>D</sub> = -8.2 A; T <sub>j</sub> = 150 °C	-	20	25	mΩ
		$V_{GS}$ = -2.5 V; I <sub>D</sub> = -3.9 A; T <sub>j</sub> = 25 °C	-	17	20	mΩ
		$V_{GS}$ = -1.8 V; I <sub>D</sub> = -3.9 A; T <sub>j</sub> = 25 °C	-	21	33	mΩ
9 <sub>fs</sub>	forward transconductance	V <sub>DS</sub> = -10 V; I <sub>D</sub> = -8.2 A; T <sub>j</sub> = 25 °C	-	40	-	S
Dynamic c	haracteristics			I		
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = -6 V; $I_{D}$ = -8.2 A; $V_{GS}$ = -4.5 V;	-	67	100	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	5.5	-	nC
Q <sub>GD</sub>	gate-drain charge		-	7.3	-	nC
C <sub>iss</sub>	input capacitance	$V_{DS}$ = -6 V; f = 1 MHz; $V_{GS}$ = 0 V;	-	2875	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	570	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	530	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = -6 V; I <sub>D</sub> = -8.2 A; V <sub>GS</sub> = -4.5 V;	-	18	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	90	-	ns
t <sub>d(off)</sub>	turn-off delay time	1	-	85	-	ns
tr	fall time		_	57	-	ns

#### Source-drain diode

source-drain voltage

 $V_{SD}$ 

I<sub>S</sub> = -1.9 A; V<sub>GS</sub> = 0 V; T<sub>j</sub> = 25 °C

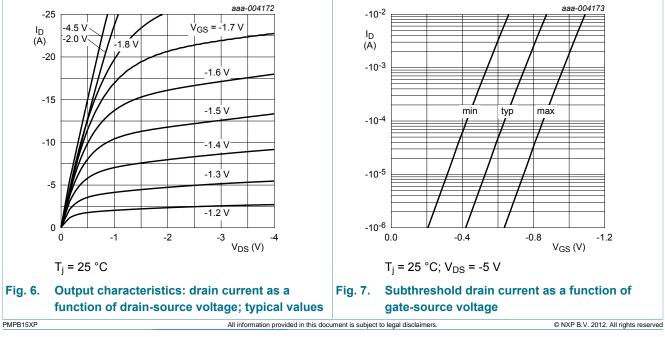
-1.2

-0.6

\_

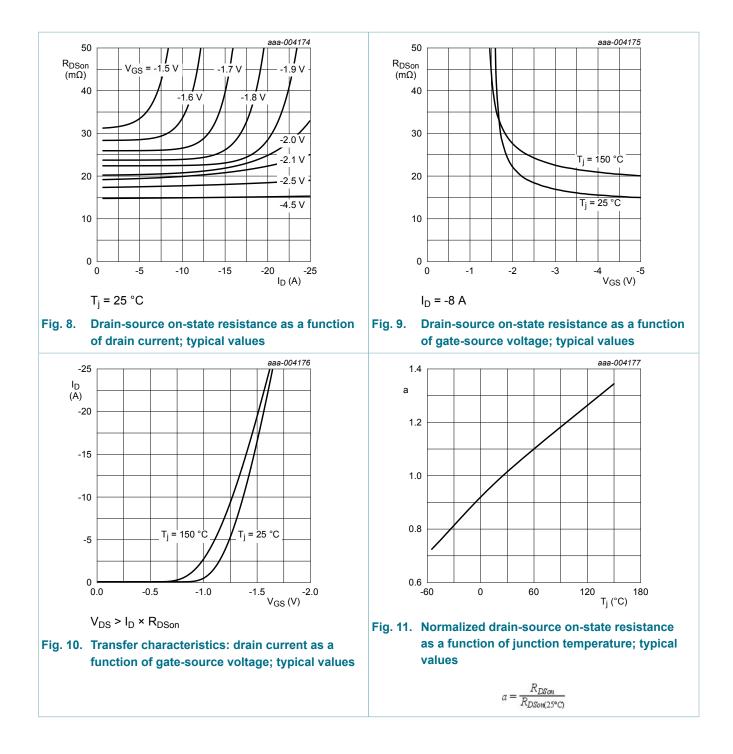
-1.2

V



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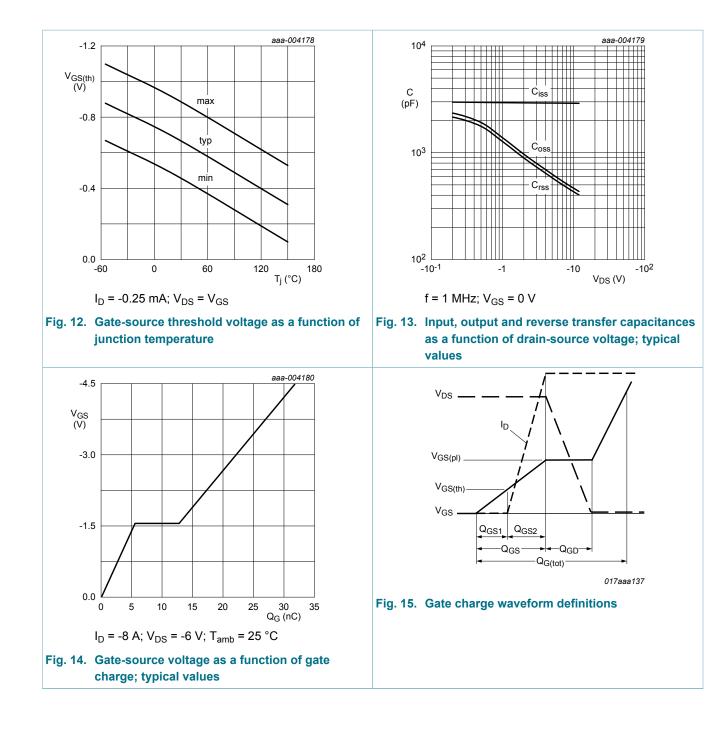
#### 12 V, single P-channel Trench MOSFET



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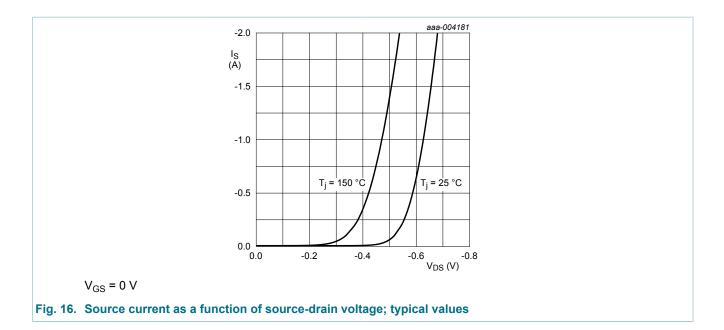


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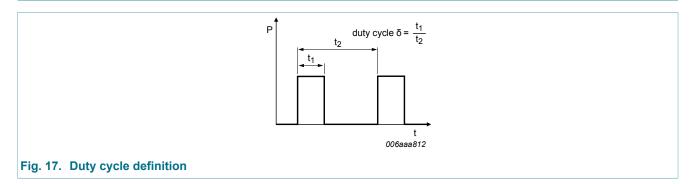
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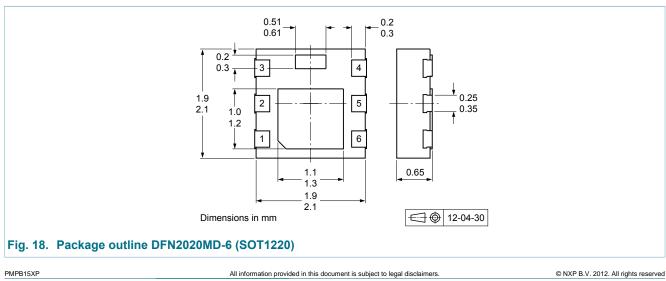
#### 12 V, single P-channel Trench MOSFET



# 8. Test information



# 9. Package outline

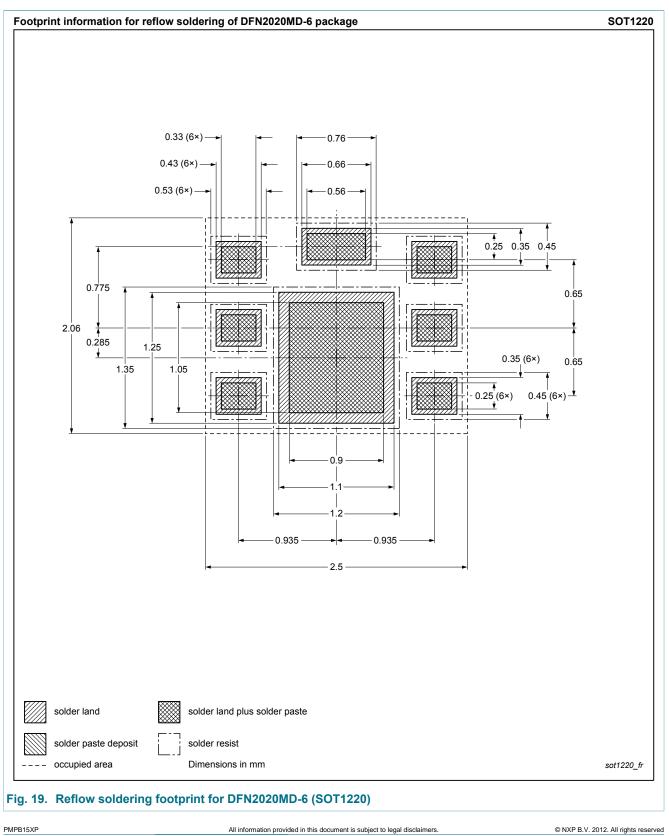


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# **10. Soldering**



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# **11. Revision history**

Table 8. Revision hi	istory			
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMPB15XP v.3	20121122	Product data sheet	-	PMPB15XP v.2
Modifications:	Table 7 "Character	ristics": R <sub>DSon</sub> at V <sub>GS</sub> = -1.	8 V corrected.	
PMPB15XP v.2	20120719	Product data sheet	-	PMPB15XP v.1
PMPB15XP v.1	20120706	Preliminary data sheet	-	-

#### 12 V, single P-channel Trench MOSFET

### 12. Legal information

#### 12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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